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IN THE CLAIMS

1. (Currently Amended) A method comprising:

soaking a substrate having a dielectric deposited thereon in an aluminum salt solution, the reactants in said aluminum salt solution available for surface reaction to range from about a few parts per million to about one percent, said dielectric having a first dielectric constant;

depositing an oxide on said dielectric, said oxide having a second dielectric constant different from the first dielectric constant; [[and]]

adjusting the pH of the aluminum salt solution; and
depositing a gate material on said oxide.

2. (Previously Presented) The method of claim 1 wherein depositing an oxide on said dielectric includes depositing primarily aluminum oxide on said dielectric.

Claim 3 (Canceled).

4. (Previously Presented) The method of claim 1 wherein soaking said substrate in said aluminum salt solution includes soaking said substrate in a salt solution comprising aluminum chloride dissolved in water.

5. (Previously Presented) The method of claim 1 wherein soaking said substrate in said aluminum salt solution includes soaking said substrate in a salt solution comprising aluminum nitrate dissolved in water.

Claims 6-7 (Canceled)

8. (Original) The method of claim 1 wherein depositing said oxide on said dielectric includes depositing said oxide on silicon dioxide.

9. (Original) The method of claim 1 wherein depositing said oxide on said dielectric includes depositing said oxide on hafnium oxide.

10. (Canceled)

11. (Previously Presented) A method comprising:

exposing a dielectric deposited on a substrate to an aluminum nitrate solution; and causing an oxide which is different from said dielectric to form on said dielectric, at least a portion of said dielectric to remain between said substrate and said oxide as part of a functional structure.

Claims 12-14 (Canceled).

15. (Previously Presented) The method of claim 11 including adjusting the pH of said aluminum nitrate solution.

16. (Previously Presented) The method of claim 11 wherein causing an oxide to deposit on said dielectric includes causing reactants in said aluminum nitrate solution to react with the top surface of said dielectric.

17. (Previously Presented) The method of claim 16 wherein causing said reactants in said aluminum nitrate solution to react with the top surface of said dielectric includes depositing an aluminum oxide layer ranging in thickness from about a few parts per million to one or more atomic layers.

18. (Previously Presented) The method of claim 11 wherein exposing said dielectric to said aluminum nitrate solution includes exposing a dielectric selected from the group consisting of silicon dioxide, hafnium dioxide and zirconia to said aluminum nitrate solution.

19. (Original) The method of claim 11 including removing said substrate from said salt solution and rinsing.

20. (Previously Presented) The method of claim 11 wherein exposing said dielectric to said aluminum nitrate solution includes exposing said dielectric to said aluminum nitrate solution for about a few seconds to about an hour.

21. (Previously Presented) A method comprising:

depositing a first oxide selected from one of hafnium oxide and zirconia on a substrate using a first method of deposition; and

depositing a second oxide other than said first oxide on said first oxide by immersing said substrate in an aluminum salt solution, the top surface of said first oxide to react with said aluminum salt solution, said deposition by immersing said substrate in the aluminum salt solution being different from said first method of deposition.

Claims 22-26 (Canceled)

27. (Previously Presented) The method of claim 21 including causing about a few parts per million of aluminum oxide to one or more atomic layers of aluminum oxide to deposit on said dielectric.

28. (Previously Presented) The method of claim 21 including adjusting the pH of said aluminum salt solution.

Claim 29 (Canceled).

30. (Previously Presented) The method of claim 21 including forming a gate material on said second oxide.

31. (Previously Presented) The method of claim 21 wherein depositing a first oxide on a substrate includes using a chemical vapor deposition technique to deposit said first oxide.

Claims 32-35 (Canceled)

36. (Previously Presented) A method comprising:

exposing a dielectric deposited on a substrate to a salt solution, the salt solution to react with an exposed surface of said dielectric to form an oxide on said dielectric other than said dielectric if said dielectric is an oxide; and

forming a layer of a gate material over said dielectric and said oxide, at least a portion of said dielectric, oxide, and gate material part of a semiconductor device after processing is complete.

Claim 37 (Canceled).

38. (Previously Presented) The method of claim 36 wherein exposing said dielectric to a salt solution includes exposing said dielectric to an aluminum salt solution.

39. (Previously Presented) The method of claim 36 wherein exposing said dielectric includes exposing one of hafnium oxide, silicon dioxide, or zirconia.

40. (Previously Presented) The method of claim 36 wherein exposing said dielectric includes exposing a dielectric to a pH adjusted salt solution.